

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A MOSFET transistor device, comprising:
a first transistor segment extending along a first axis; including
a plurality of first source regions formed in a semiconductor body, the first source regions extending on laterally opposite sides of the first axis;
a plurality of first drain regions formed in the semiconductor body, the first drain regions extending on laterally opposite sides of the first axis;
a plurality of first gate structures formed over a plurality of channel regions in a semiconductor body, the first gate structures extending on laterally opposite sides of the first axis;
a conductive first source interconnect structure extending generally parallel with the first axis from a first end to a second end of the first transistor segment, the first source interconnect structure being electrically coupled with the plurality of first source regions in the semiconductor body; and
a conductive first drain interconnect structure extending generally parallel with the first axis from the first end to the second end of the first transistor segment, the first drain interconnect structure being electrically coupled with the plurality of first drain regions in the semiconductor body; and
a second transistor segment extending along a second axis;
wherein the first and second transistor segments are contiguous, the first axis and the second ~~transistor segments~~ axis are not ~~non-coaxial~~ collinear.
2. (original) The transistor device of claim 1, wherein the first axis and the second axis are perpendicular.

3. (canceled)

4. (original) The transistor device of claim 2, wherein at least one of the first axis and the second axis is straight.

5 – 7. (canceled)

8. (currently amended) The transistor device of claim [7] 1, wherein the second transistor segment comprises:

a plurality of second source regions formed in a semiconductor body, the second source regions extending on laterally opposite sides of the second axis;

a plurality of second drain regions formed in the semiconductor body, the second drain regions extending on laterally opposite sides of the second axis;

a plurality of second gate structures formed over channel regions of the semiconductor body, the second gate structures extending on laterally opposite sides of the second axis;

a conductive second source interconnect structure extending generally parallel with the second axis from [the] ~~a second~~ first end to [the] a second end of the second transistor segment, the second source interconnect structure being electrically coupled with the plurality of second source regions in the semiconductor body; and

a conductive second drain interconnect structure extending generally parallel with the second axis from the ~~second~~ first end to the second end of the second transistor segment, the second drain interconnect structure being electrically coupled with the plurality of second drain regions in the semiconductor body.

9 – 14. (canceled)

15. (original) The transistor device of claim 1, wherein the transistor device has an effective aspect ratio greater than about 5.

16. (original) The transistor device of claim 1, wherein the transistor device has an effective aspect ratio greater than about 10.

17 – 21. (canceled)

22. (new) A MOSFET transistor device comprising:

source members, gate members, and drain members disposed near a surface of a semiconductor wafer, each gate member adjacent to a source member and a drain member;

contiguous first and second segments of a first conductive member connecting the source members electrically;

contiguous first and second segments of a second conductive member connecting the drain members electrically;

contiguous first and second segments of a third conductive member connecting the gate members electrically; and

wherein the first segments of the conductive members are substantially parallel and the second segments of the conductive members are substantially parallel; and

the first segment and the second segment of the first conductive member are not collinear.

23. (new) The MOSFET transistor device of claim 22, wherein the first conductive member further includes a third segment connecting the source members and the third segment is contiguous to and not collinear with the second segment of the first conductive member.

24. (new) The MOSFET transistor device of claim 22, further comprising circuit-blocks.

25. (new) The MOSFET transistor device of claim 24, in which a circuit-block comprises a digital circuitry.

26. (new) The MOSFET transistor device of claim 24, in which a circuit-block comprises an analog circuitry.

27. (new) The MOSFET transistor device of claim 24, in which a circuit-block comprises bipolar devices.
28. (new) The MOSFET transistor device of claim 25, in which the digital circuitry comprises microprocessors, A/D converters, or their combinations.
29. (new) The MOSFET transistor device of claim 26, in which the analog circuitry comprises op-amps, comparators, bandgap voltage references, A/D converters, or their combinations.
30. (new) The MOSFET transistor device of claim 22, further comprising parasitic bipolar transistor circuitry.
31. (new) The MOSFET transistor device of claim 26, further comprising a LMOS transistor.
32. (new) The MOSFET transistor device of claim 24, in which the first and the second segments of the first conductive member are interspersed between circuit-blocks.
33. (new) A bipolar transistor device comprising:

emitter members, base members, and collector members disposed near a surface of a semiconductor wafer wherein each base member is adjacent to an emitter member and a collector member;

contiguous first and second segments of a first conductive member connecting the emitter members electrically;

contiguous first and second segments of a second conductive member connecting the base members electrically; and

contiguous first and second segments of a third conductive member connecting the drain members electrically; and

wherein the first segments of the conductive members are substantially parallel and the second segments of the conductive members are substantially parallel;

and the first segment and the second segment of the first conductive member are not collinear.

34. (new) The bipolar transistor device of claim 33, wherein the first conductive member further includes a third segment connecting the emitter members and the third segment is contiguous to and not collinear with the second segment of the first conductive member.

35. (new) The bipolar transistor device of claim 33, further comprising circuit-blocks of analog and digital circuitry, and the first and second segments of the first conductive member interspersed between the circuit-blocks.